

GT35J321

Fourth-generation IGBT

Current Resonance Inverter Switching Applications

- Enhancement mode
- High speed: $t_f = 0.19 \mu s$ (typ.) ($I_C = 50 A$)
- Low saturation voltage: $V_{CE(sat)} = 1.9 V$ (typ.) ($I_C = 50 A$)
- FRD included between emitter and collector
- Toshiba package name: TO-3P(N)IS

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Collector-emitter voltage		V_{CES}	600	V
Gate-emitter voltage		V_{GES}	± 25	V
Collector current (DC)	@ $T_c = 100^\circ\text{C}$	I_C	18	A
	@ $T_c = 25^\circ\text{C}$		37	
Collector current (pulse)		I_{CP}	100	A
Diode forward current	DC	I_F	20	A
	Pulse	I_{FP}	40	
Collector power dissipation	@ $T_c = 100^\circ\text{C}$	P_C	30	W
	@ $T_c = 25^\circ\text{C}$		75	
Junction temperature		T_j	150	$^\circ\text{C}$
Storage temperature range		T_{stg}	-55 to 150	$^\circ\text{C}$

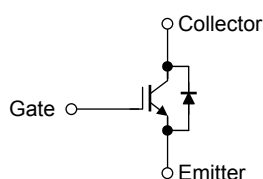
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

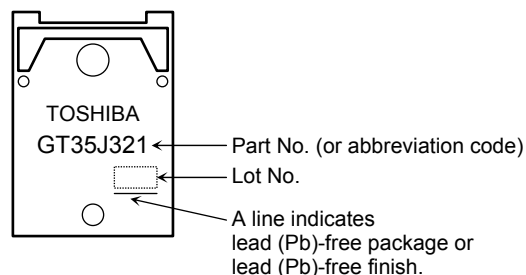
Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance (IGBT)	R _{th(j-c)}	1.67	°C/W
Thermal resistance (diode)	R _{th(j-c)}	3.2	°C/W

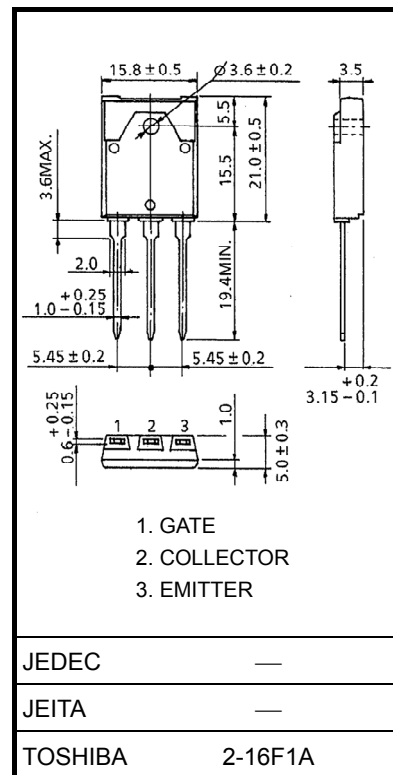
Equivalent Circuit



Marking



Unit: mm

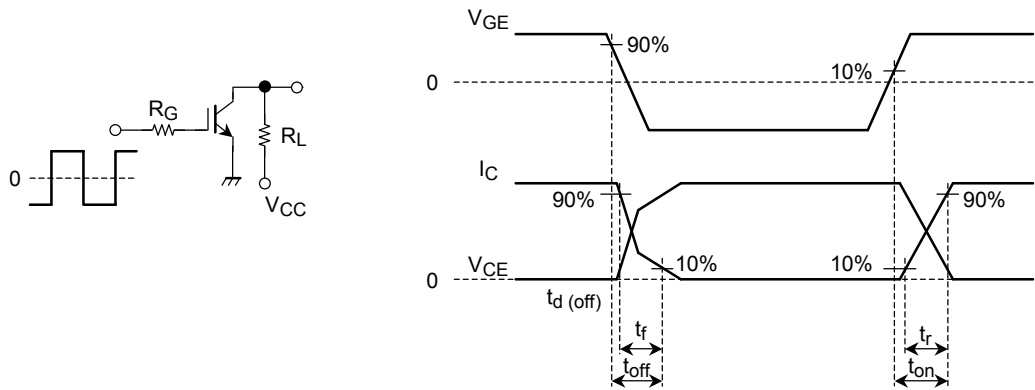


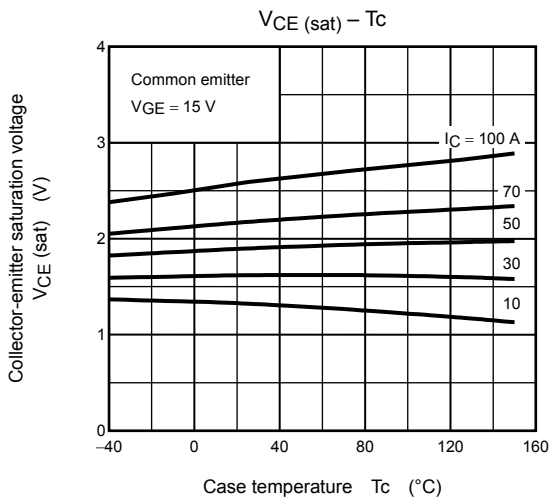
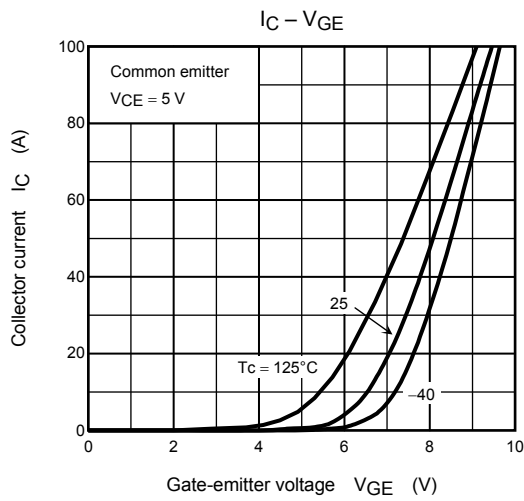
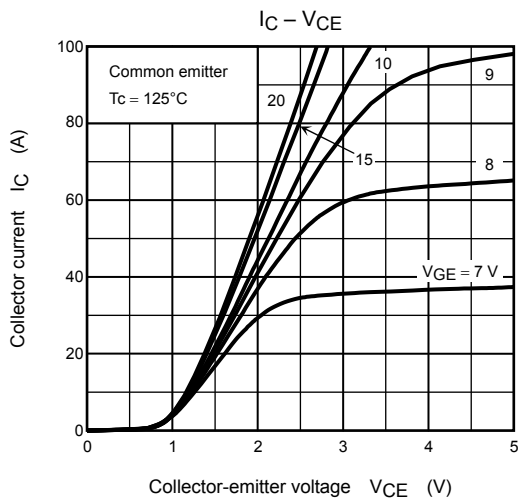
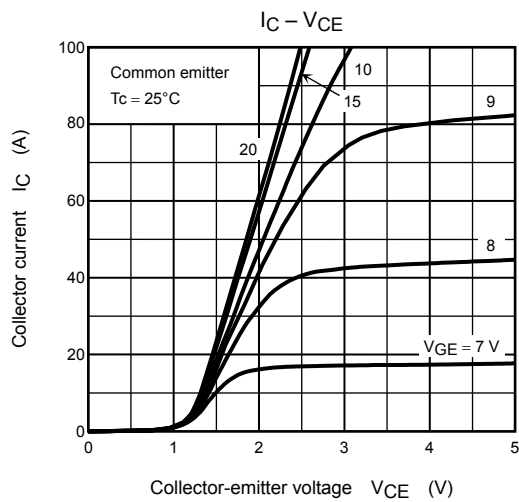
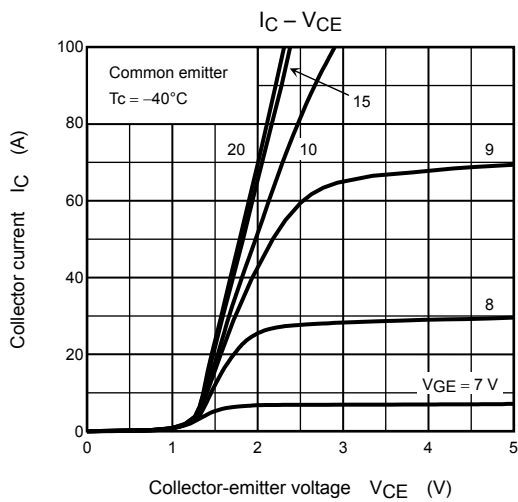
Weight: 5.8 g (typ.)

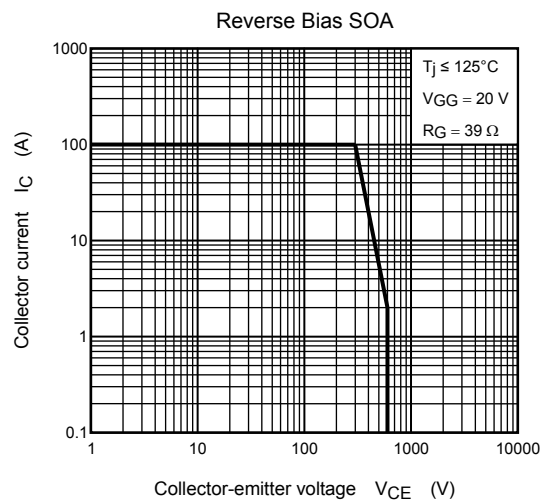
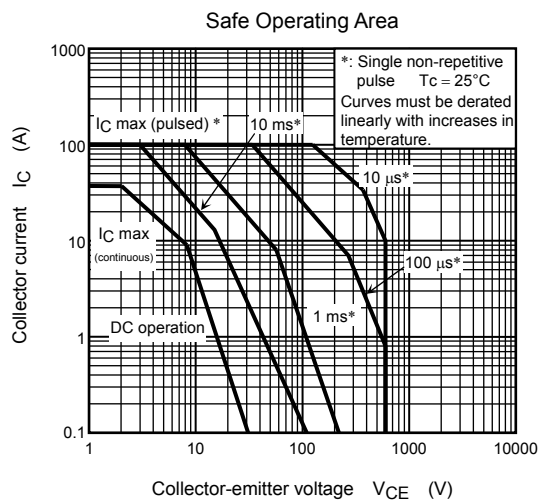
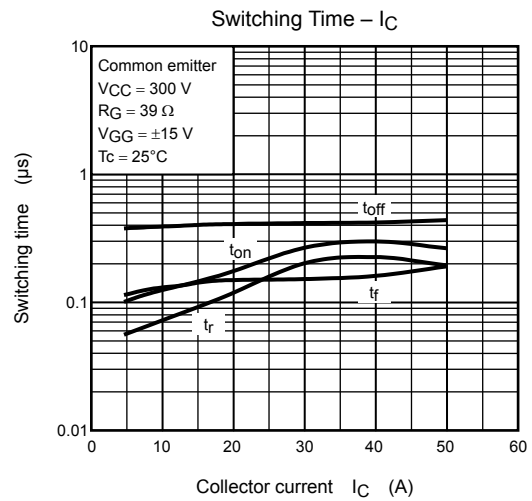
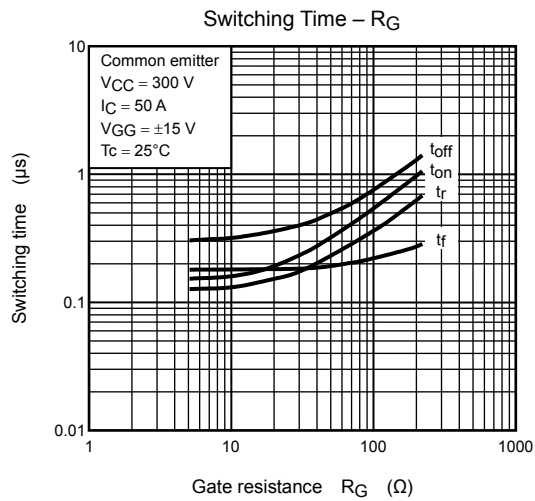
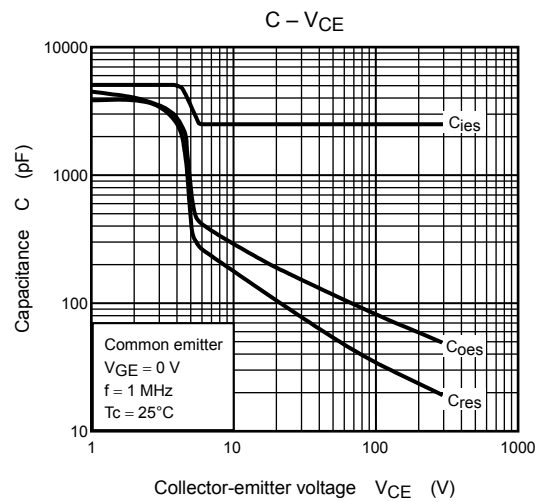
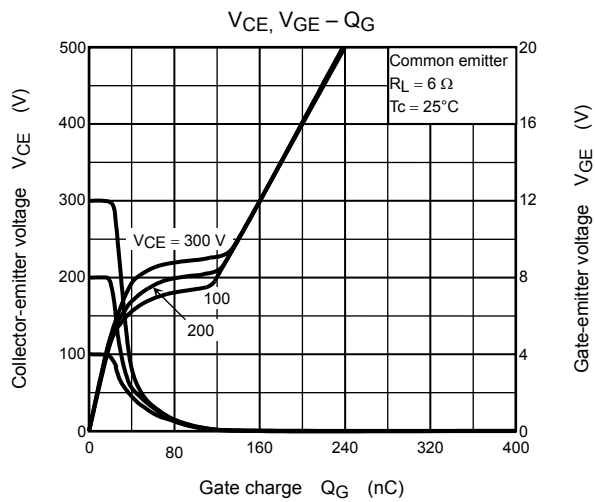
Electrical Characteristics (Ta = 25°C)

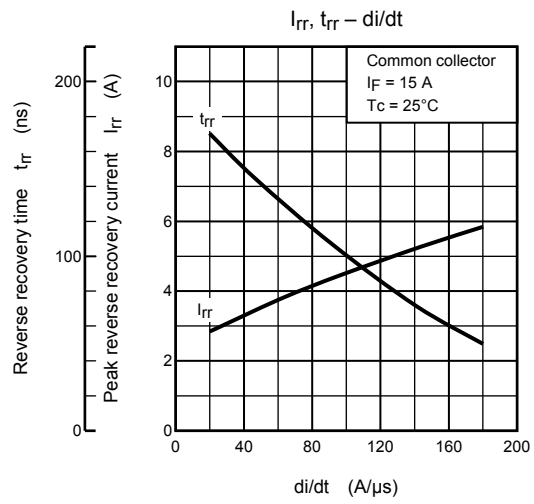
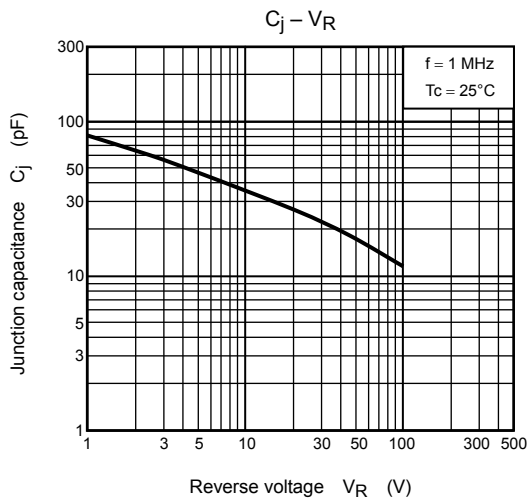
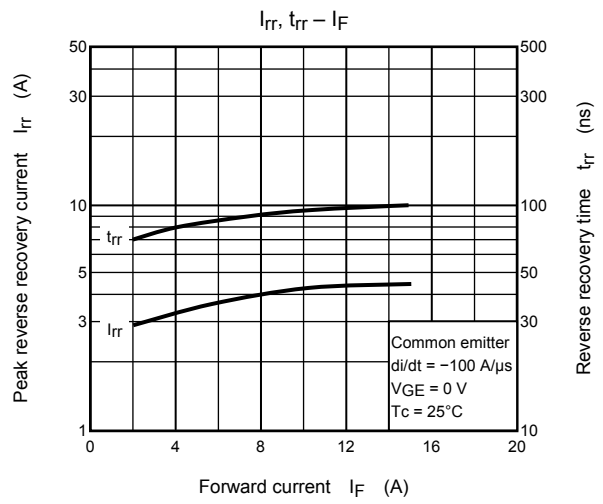
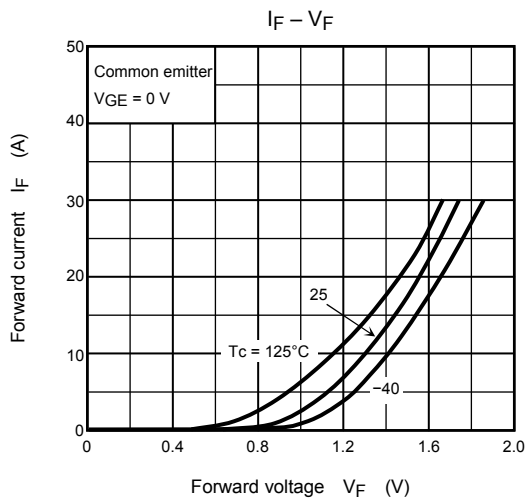
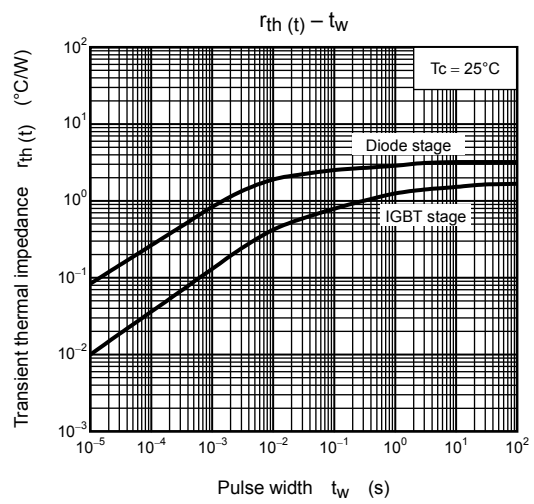
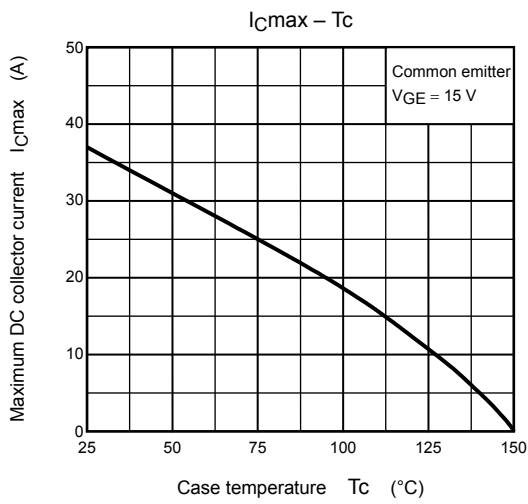
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GES}	$V_{GE} = \pm 25 \text{ V}, V_{CE} = 0 \text{ V}$	—	—	± 500	nA
Collector cut-off current		I_{CES}	$V_{CE} = 600 \text{ V}, V_{GE} = 0 \text{ V}$	—	—	1.0	mA
Gate-emitter cut-off voltage		$V_{GE}(\text{OFF})$	$I_C = 50 \text{ mA}, V_{CE} = 5 \text{ V}$	3.0	—	6.0	V
Collector-emitter saturation voltage		$V_{CE}(\text{sat})$	$I_C = 50 \text{ A}, V_{GE} = 15 \text{ V}$	—	1.9	2.3	V
Input capacitance		C_{ies}	$V_{CE} = 10 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$	—	2500	—	pF
Switching time	Rise time	t_r	Resistive Load $V_{CC} = 300 \text{ V}, I_C = 50 \text{ A}$ $V_{GG} = \pm 15 \text{ V}, R_G = 39 \Omega$ (Note 1)	—	0.24	—	μs
	Turn-on time	t_{on}		—	0.33	—	
	Fall time	t_f		—	0.19	0.32	
	Turn-off time	t_{off}		—	0.51	—	
Diode forward voltage		V_F	$I_F = 15 \text{ A}, V_{GE} = 0 \text{ V}$	—	—	2.0	V
Reverse recovery time		t_{rr}	$I_F = 15 \text{ A}, di/dt = -100 \text{ A}/\mu\text{s}$	—	—	0.2	μs

Note 1: Switching time measurement circuit and input/output waveforms









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20070701-EN GENERAL

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